

APM2023N

N-Channel Enhancement Mode MOSFET

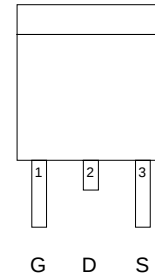
Features

- 20V/12.8A , $R_{DS(ON)}=20m\Omega(\text{typ.}) @ V_{GS}=4.5V$
 $R_{DS(ON)}=29m\Omega(\text{typ.}) @ V_{GS}=2.5V$
- Super High Dense Cell Design for Extremely Low $R_{DS(ON)}$
- Reliable and Rugged
- TO-252 Package

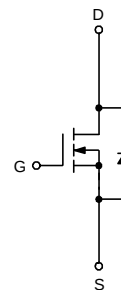
Applications

- Power Management in Notebook Computer ,
 Portable Equipment and Battery Powered
 Systems.

Pin Description



Top View of TO-252



N-Channel MOSFET

Ordering and Marking Information

APM2023N - Handling Code Temp. Range Package Code	Package Code U : TO-252 Operation Junction Temp. Range C : -55 to 150°C Handling Code TR : Tape & Reel
APM2023N U :	 XXXXX - Date Code

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	± 12	
I_D^*	Maximum Drain Current – Continuous	12.8	A
I_{DM}	Maximum Drain Current – Pulsed	50	

* Surface Mounted on FR4 Board, $t \leq 10$ sec.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

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Absolute Maximum Ratings (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	W
		$T_A=100^\circ\text{C}$	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance – Junction to Ambient	50	$^\circ\text{C/W}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	APM2023N			Unit
			Min.	Typ.	Max.	
Static						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _{DS} =250μA	18			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V , V _{GS} =0V			1	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	0.5	0.7	1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±12V , V _{DS} =0V			±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =4.5V , I _{DS} =12.8A		20	23	mΩ
		V _{GS} =2.5V , I _{DS} =6.6A		29	35	
V _{SD} ^a	Diode Forward Voltage	I _{SD} =1.7A , V _{GS} =0V		0.8	1.1	V
Dynamic ^b						
Q _g	Total Gate Charge	V _{DS} =10V , I _{DS} = 6A V _{GS} =4.5V ,		15	18	nC
Q _{gs}	Gate-Source Charge			5.4		
Q _{gd}	Gate-Drain Charge			3		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =10V , I _{DS} =1A , V _{GEN} =4.5V , R _G =0.2Ω		25	47	ns
T _r	Turn-on Rise Time			21	42	
t _{d(OFF)}	Turn-off Delay Time			65	120	
T _f	Turn-off Fall Time			35	65	
C _{iss}	Input Capacitance	V _{GS} =0V		780		pF
C _{oss}	Output Capacitance	V _{DS} =15V		165		
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz		105		

Notes

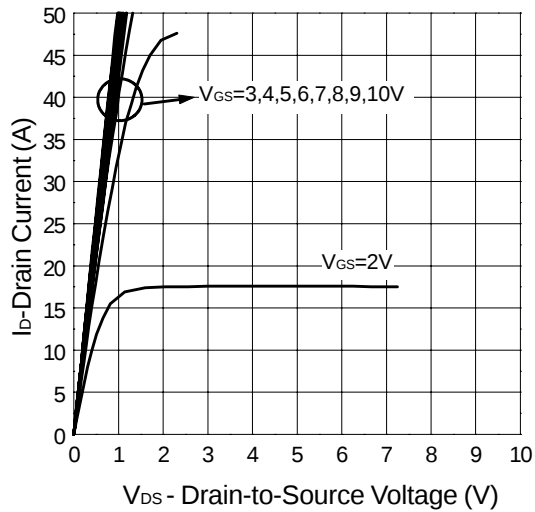
^a : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$

^b : Guaranteed by design, not subject to production testing

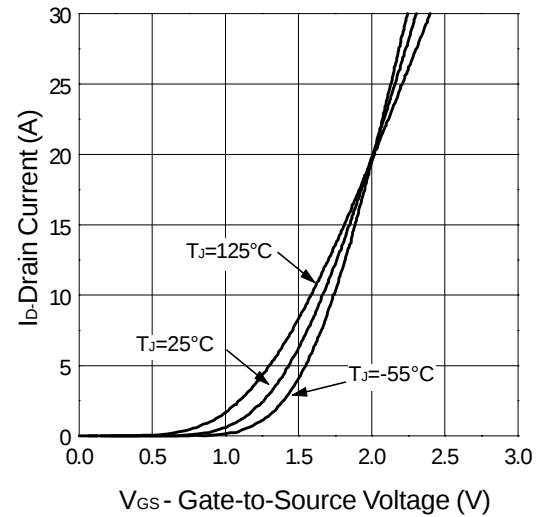
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Typical Characteristics

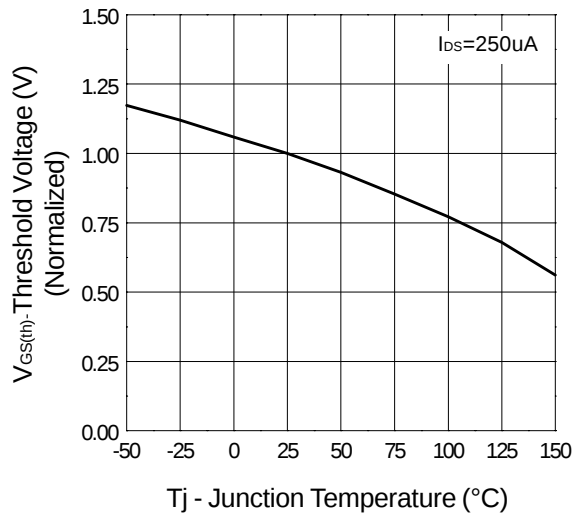
Output Characteristics



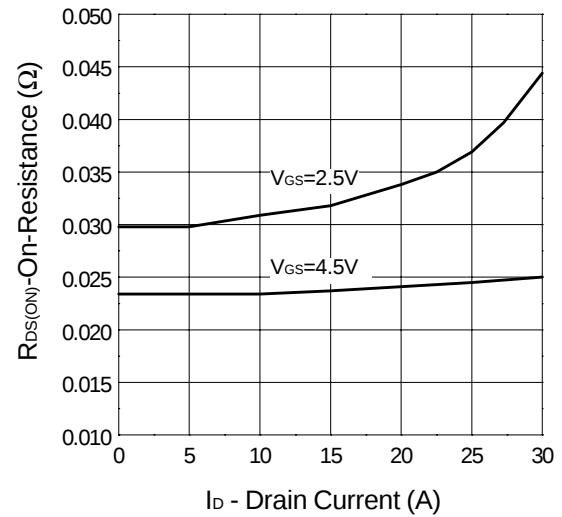
Transfer Characteristics



Threshold Voltage vs. Junction Temperature



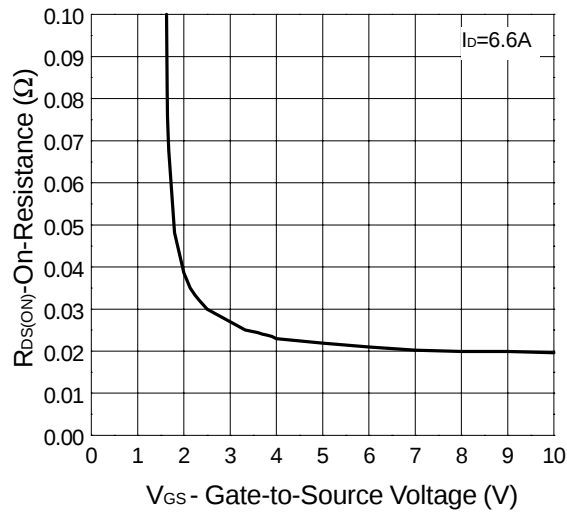
On-Resistance vs. Drain Current



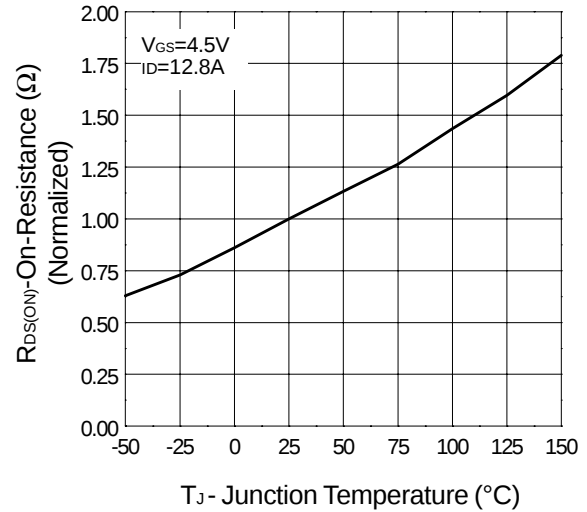
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Typical Characteristics

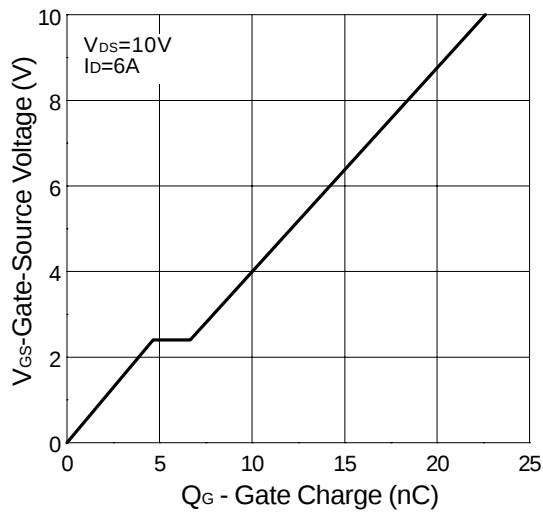
On-Resistance vs. Gate-to-Source Voltage



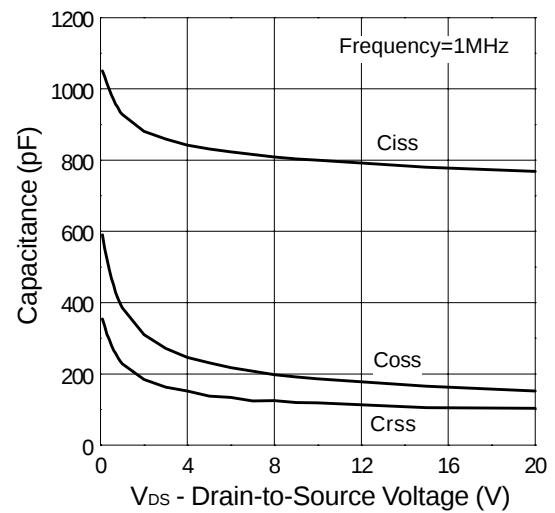
On-Resistance vs. Junction Temperature



Gate Charge

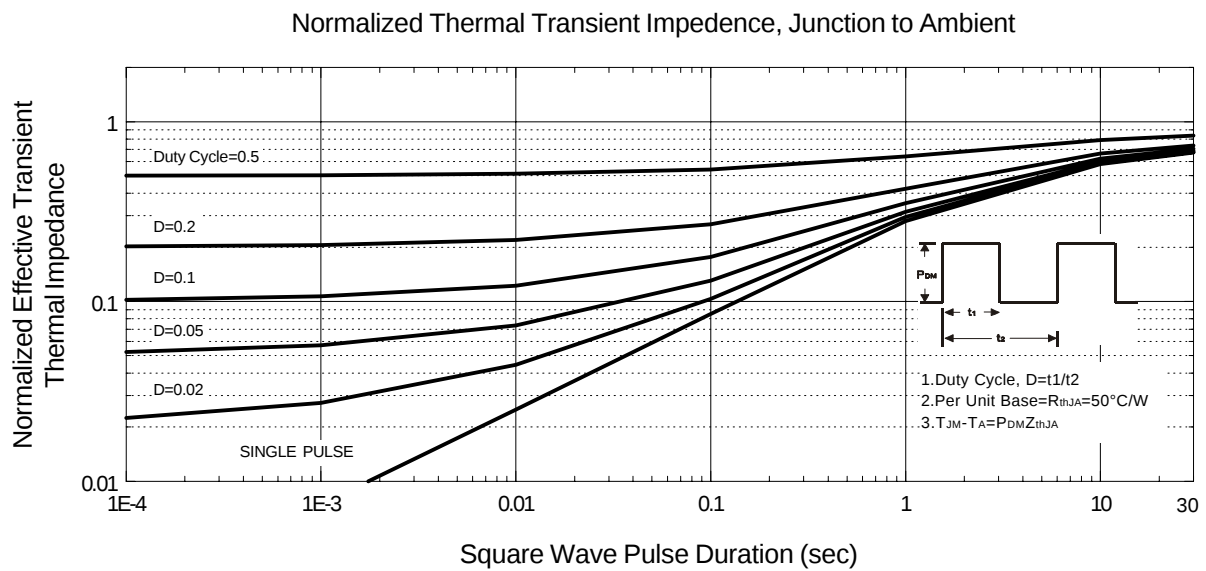
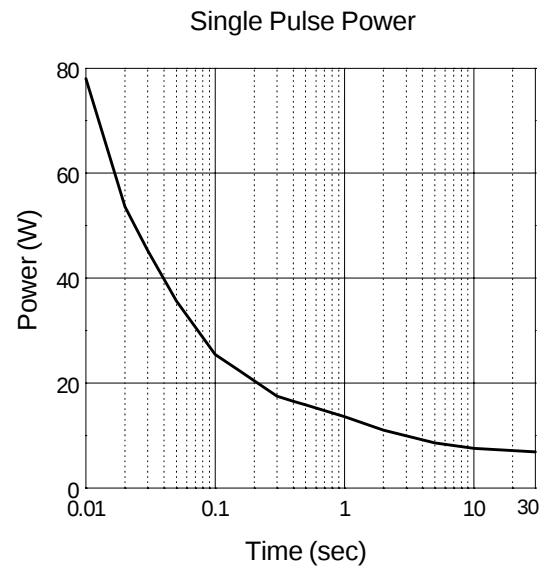
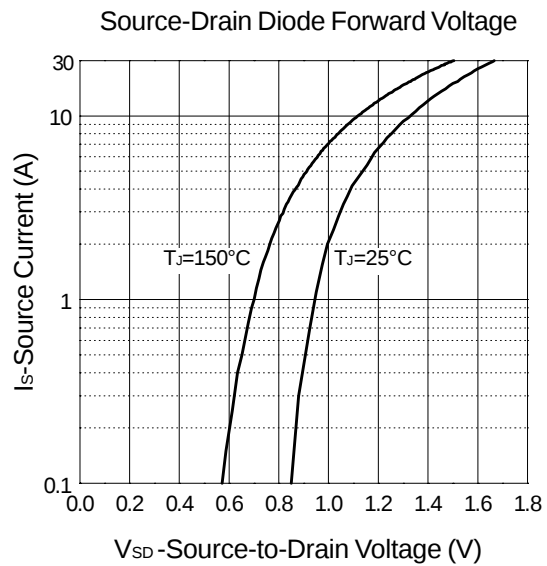


Capacitance



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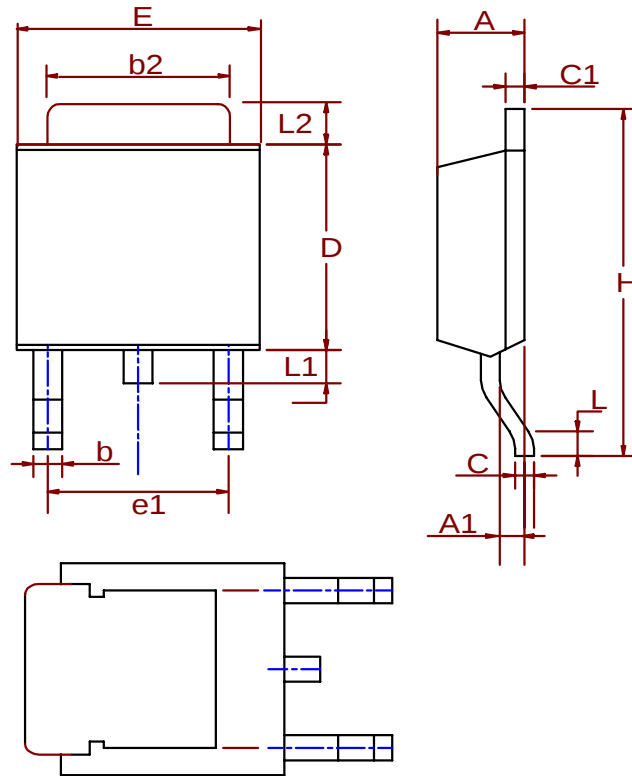
Typical Characteristics



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Packaging Information

TO-252 (Reference JEDEC Registration TO-252)



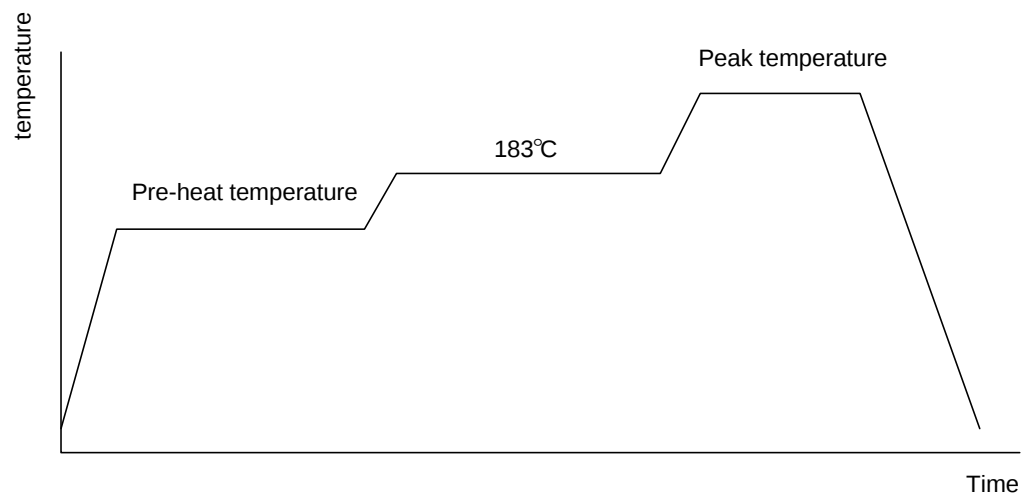
Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.18	2.39	0.086	0.094
A1	0.89	1.27	0.035	0.050
b	0.508	0.89	0.020	0.035
b2	5.207	5.461	0.205	0.215
C	0.46	0.58	0.018	0.023
C1	0.46	0.58	0.018	0.023
D	5.334	6.22	0.210	0.245
E	6.35	6.73	0.250	0.265
e1	3.96	5.18	0.156	0.204
H	9.398	10.41	0.370	0.410
L	0.51		0.020	
L1	0.64	1.02	0.025	0.040
L2	0.89	2.032	0.035	0.080

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Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb)
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)



Classification Reflow Profiles

	Convection or IR/ Convection	VPR
Average ramp-up rate(183°C to Peak)	3°C/second max.	10 °C /second max.
Preheat temperature 125 ± 25°C)	120 seconds max	
Temperature maintained above 183°C	60 – 150 seconds	
Time within 5°C of actual peak temperature	10 –20 seconds	60 seconds
Peak temperature range	220 +5/-0°C or 235 +5/-0°C	215-219°C or 235 +5/-0°C
Ramp-down rate	6 °C /second max.	10 °C /second max.
Time 25°C to peak temperature	6 minutes max.	

Package Reflow Conditions

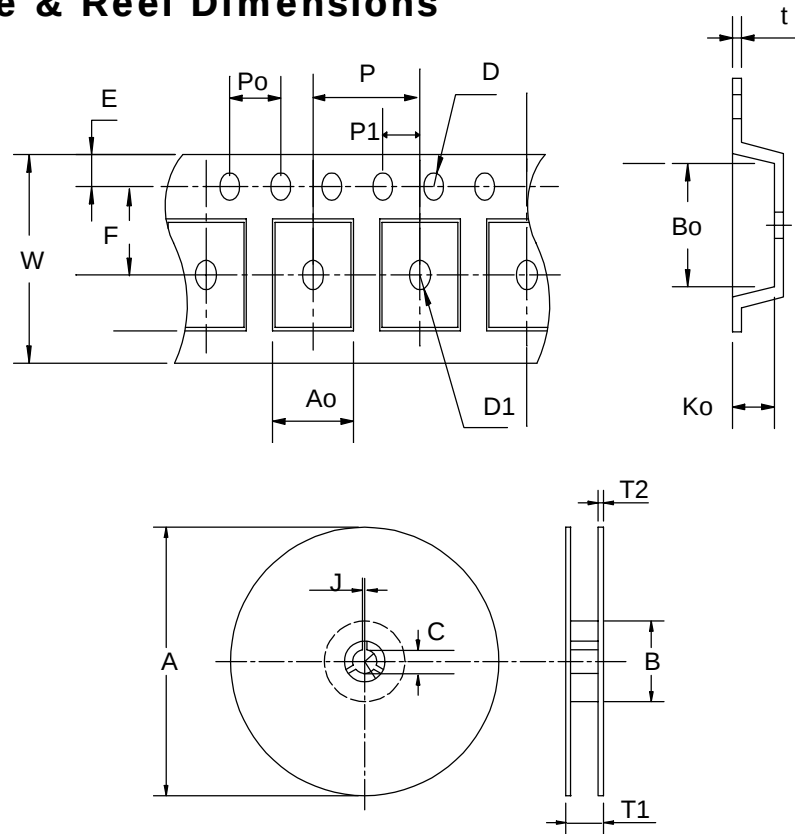
pkg. thickness ≥ 2.5mm and all bgas	pkg. thickness < 2.5mm and pkg. volume ≥ 350 mm ³	pkg. thickness < 2.5mm and pkg. volume < 350mm ³
Convection 220 +5/-0 °C		Convection 235 +5/-0 °C
VPR 215-219 °C		VPR 235 +5/-0 °C
IR/Convection 220 +5/-0 °C		IR/Convection 235 +5/-0 °C

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Reliability test program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

Carrier Tape & Reel Dimensions



Application	A	B	C	J	T1	T2	W	P	E
TO-252	330 ± 3	100 ± 2	13 ± 0.5	2 ± 0.5	16.4 +0.3 -0.2	2.5 ± 0.5	16 +0.3 -0.1	8 ± 0.1	1.75 ± 0.1
	F	D	D1	P0	P1	A0	Bo	K0	t
	7.5 ± 0.1	1.5 ± 0.1	1.5 ± 0.25	4.0 ± 0.1	2.0 ± 0.1	6.8 ± 0.1	10.4 ± 0.1	2.5 ± 0.1	0.3 ± 0.05

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Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
TO- 252	16	13.3	2500

Customer Service

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